



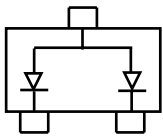
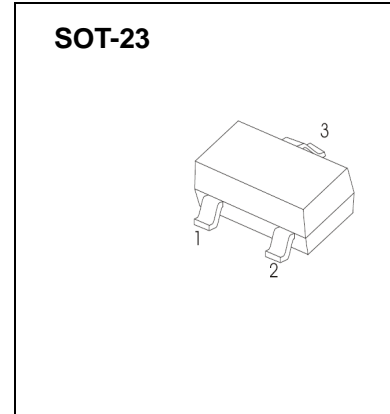
TIGER ELECTRONIC CO.,LTD

SOT-23 Plastic-Encapsulate Diodes

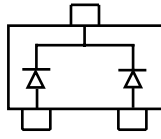
BAW56/BAV70/BAV99 SWITCHING DIODE

FEATURES

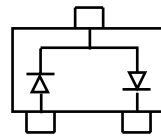
- Fast Switching Speed
- For General Purpose Switching Applications
- High Conductance



BAW56 Marking: A1



BAV70 Marking: A4



BAV99 Marking: A7

Maximum Ratings @Ta=25°C

Parameter	Symbol	Limit	Unit
Reverse Voltage	V_R	70	V
Forward Current	I_F	200	mA
Peak Forward Surge Current	$I_{FM(surge)}$	500	mA
Power Dissipation	P_D	225	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/W
Junction Temperature	T_J	150	°C
Storage Temperature range	T_{STG}	-55~+150	°C

Electrical Characteristics @Ta=25°C

Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Reverse breakdown voltage	V_R	70			V	$I_R=100\mu A$
Forward voltage	V_{F1}			0.715	V	$I_F=1mA$
	V_{F2}			0.855	V	$I_F=10mA$
	V_{F3}			1	V	$I_F=50mA$
	V_{F4}			1.25	V	$I_F=150mA$
Reverse current	I_R			2.5	μA	$V_R=70V$
Capacitance between terminals	C_T			1.5	pF	$V_R=0, f=1MHz$
Reverse recovery time	t_{rr}			6	ns	$I_F = I_R = 10mA,$ $I_{rr} = 0.1 \times I_R, R_L = 100\Omega$

Typical Characteristics

BAV99

